Vishay Siliconix

# Automotive P-Channel 150 V (D-S) 175 °C MOSFET

# PowerPAK® 1212-8W Single D D D B T Top View Bottom View

Marking Code: Q026

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	-150
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -10 \text{ V}$	1.095
I <sub>D</sub> (A)	-4.7
Configuration	Single
Package	PowerPAK 1212-8W

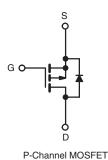
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified <sup>d</sup>
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	-150	V	
Gate-source voltage	V <sub>GS</sub>	± 20	V		
Continuous drain current <sup>a</sup>	T <sub>C</sub> = 25 °C	1	-4.7	A	
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	-2.75		
Continuous source current (diode conduction	on) <sup>a</sup>	I <sub>S</sub>	-8		
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	-19		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-4		
Single pulse avalanche energy	L=0.1 IIII	E <sub>AS</sub>	0.8	mJ	
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	62.5	W	
	T <sub>C</sub> = 125 °C	$P_{D}$	20	VV	
Operating junction and storage temperature	e range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) e, f			260	٠.	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	$R_{thJA}$	81	°C/W
Junction-to-case (drain)		$R_{thJC}$	2.4	C/ VV

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing
- e. See solder profile (<a href="https://www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK 1212-8W is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



# Vishay Siliconix

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static					•	l		
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0$ , $I_D = -250 \mu A$		-150	-	-	.,	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-2.5	-3	-3.5	V	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -150 V	-	-	-1		
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -150 V, T <sub>J</sub> = 125 °C	-	-	-50	μΑ	
		$V_{GS} = 0 V$ $V_{DS} =$	V <sub>DS</sub> = -150 V, T <sub>J</sub> = 175 °C	-	-	-150		
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \ge 5 \text{ V}$	-5	-	-	Α	
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -2.4 A	-	0.910	1.095		
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -2.4 A, T <sub>J</sub> = 125 °C	-	-	2.290	Ω	
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -2.4 A, T <sub>J</sub> = 175 °C	-	-	2.570		
Forward transconductance b	9 <sub>fs</sub>	$V_{DS}$	= -15 V, I <sub>D</sub> = -1 A	-	2.5	-	S	
Dynamic <sup>b</sup>								
Input capacitance	C <sub>iss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -75 V, f = 1 MHz	-	305	385		
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -75 V, f = 1 MHz	-	18	24	pF	
Reverse transfer capacitance	C <sub>rss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -75 V, f = 1 MHz	-	10	13		
Total gate charge <sup>c</sup>	Qg	V <sub>GS</sub> = -10 V	$V_{DS} = -75 \text{ V}, I_{D} = -1 \text{ A}$	-	8	11		
Gate-source charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = -10 V	$V_{DS} = -75 \text{ V}, I_{D} = -1 \text{ A}$	-	1.7	-	nC	
Gate-drain charge <sup>c</sup>	$Q_{gd}$	V <sub>GS</sub> = -10 V	$V_{DS} = -75 \text{ V}, I_{D} = -1 \text{ A}$	-	2.5	-		
Gate resistance	$R_g$		f = 1 MHz	2.8	4.7	7.6	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	7.1	10		
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$= -75 \text{ V}, \text{ R}_{\text{L}} = 75 \Omega$	-	2.3	3.3	200	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	I <sub>D</sub> ≅ -1 A,	$V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$	-	15.3	21.5	ns	
Fall time <sup>c</sup>	t <sub>f</sub>	]		-	2.6	3.8		
Source-Drain Diode Ratings and Char	acteristic <sup>b</sup>							
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-20	Α	
Forward voltage	$V_{SD}$	le =	: -5 A, V <sub>GS</sub> = 0 V	-	-0.8	-1.1	V	

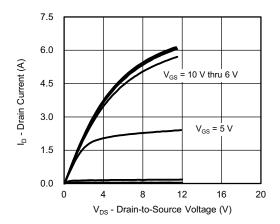
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

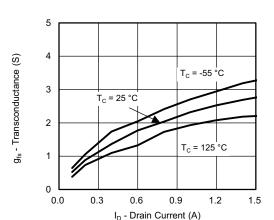
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



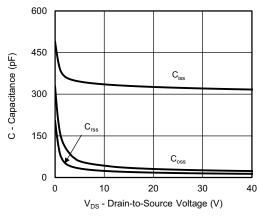
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



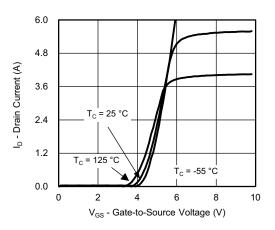
#### **Output Characteristics**



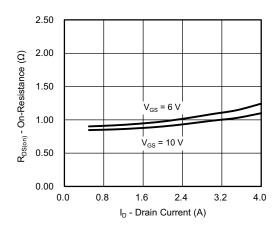
Transconductance



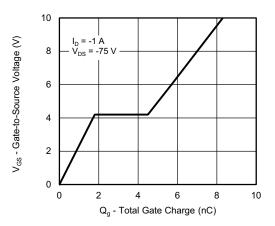
Capacitance



**Transfer Characteristics** 



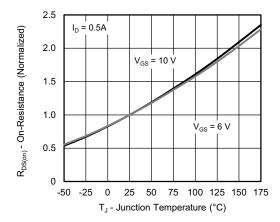
On-Resistance vs. Drain Current



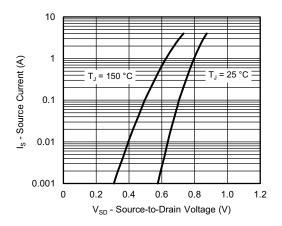
**Gate Charge** 



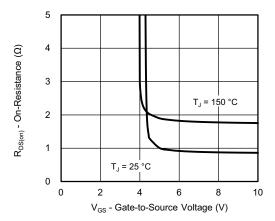
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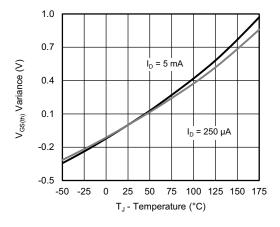
On-Resistance vs. Junction Temperature



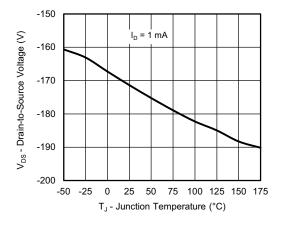
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to-Source Voltage



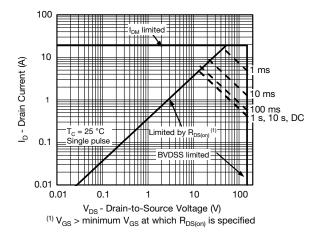
**Threshold Voltage** 



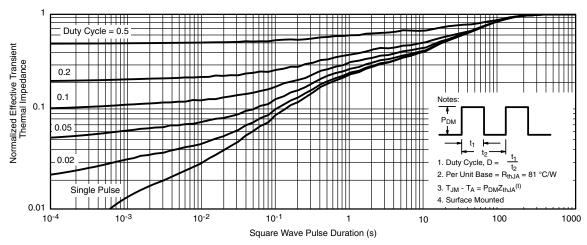
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



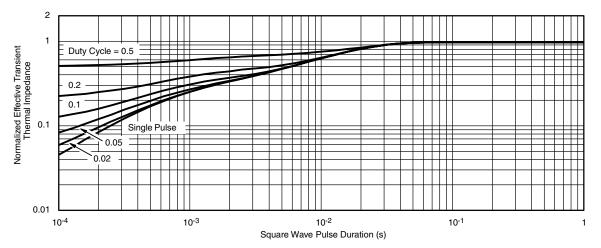
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

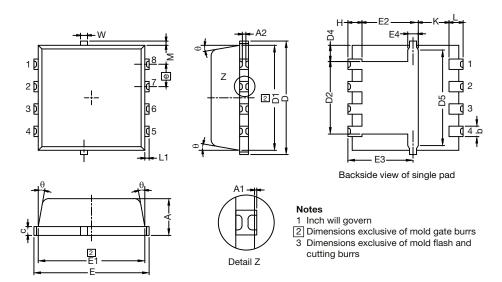
- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg276468">www.vishay.com/ppg276468</a>.



# PowerPAK® 1212-8W Case Outline



DIM.		MILLIMETERS		INCHES			
DINI.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0	-	0.05	0	-	0.002	
A2	0	-	0.13	0	-	0.005	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D4	0.47 typ.				0.0185 typ.		
D5		2.3 typ.		0.090 typ.			
Е	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4		0.34 typ.			0.013 typ.		
е		0.65 BSC.		0.026 BSC			
K		0.86 typ.		0.034 typ.			
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М		0.125 typ.			0.005 typ.		

DWG: 6032



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